

700V GaN Power Transistor

Description

Product Summary					
V _{DS} (V)	$R_{DS(on)}(m\Omega)(Typ)$	I _D (A)			
700	125	11			

Feature

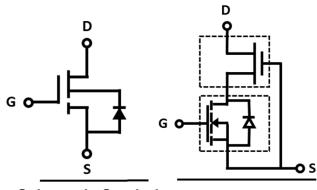
- > Easy to use, compatible with standard gate drivers
- ➤ Excellent Q_G x R_{DS(on)} figure of merit (FOM)
- ightharpoonup Low \mathbf{Q}_{RR} , no free-wheeling diode required
- ➤ Low switching loss
- > RoHS compliant and Halogen-free

Applications

- ➤ High efficiency power supplies
- > Telecom and datacom
- > Automotive
- Servo motors



TO-220F (Top View)



Schematic Symbol

Cascode **Device Structure**

Absolute maximum rating@25°C

Parameter		Symbol	Rating	Unit	
Drain-Source Voltage		V _{DS}	700	V	
Gate-Source Voltage		V _{GS}	±20	V	
Transient Drain-Source Voltage ¹⁾		V _{TDS}	800	V	
Continuous Dunin Comment	T _C =25°C		11	А	
Continuous Drain Current	T _C =100°C	- I _D	7		
Duland Dunin Courset (Dulan Width, 1000a)	T _C =25°C		49	А	
Pulsed Drain Current (Pulse Width: 100μs)	T _C =150°C	I _{DM}	37		
Power Dissipation	P _D	28	W		
Soldering Peak Temperature		T _{CSOLD}	260	°C	
Operating Junction and Storage Temperature		T _{J,} T _{STG}	-55 to 150	°C	

Thermal Resistance

Parameter	Symbol	Min	Тур	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	-	4.4	-	°C/W
Thermal Resistance, Junction-to-Ambient ²⁾	$R_{\theta JA}$	-	50	-	°C/W

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions		Min.	Тур.	Max.	Units
Statistic Characteristics							
Maximum Drain-Source Voltage	V _{DS-Max}	V _{GS} = 0V		700	-	-	V
Drain-Source Breakdown Voltage	BV _{DSS}	$V_{GS} = 0V, I_{D} = 250\mu A$		-	1000	-	V
Zero Gate Voltage Drain Current		V _{DS} =700V, V _{GS} =0V	T _J =25°C	-	8	20	0 μΑ
Zero Gate voltage Drain Current	l _{DSS}		T _J =150°C	-	50	-	
Gate-Body Leakage Current	I _{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$		ı	-	±150	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 500 \mu A$		3	4	5	V
Gate threshold voltage temperature coefficient	$\triangle V_{GS(th)}/T_J$			•	-10.7	-	mV/°C
Drain-Source On-State Resistance ³⁾	D	V _{GS} =12V, I _D =4A	T _J =25℃	-	125	160	mΩ
Dialif-Source Off-State Resistance	$R_{DS(ON)}$	I _D =4A	T _J =150°C	ı	250	-	
Dynamic Characteristics							
Input Capacitance	C _{lss}	$V_{DS} = 400V, V_{GS} = 0V,$ f = 1MHz		ı	524	-	pF
Output Capacitance	C _{oss}			ı	29	-	
Reverse Transfer Capacitance	C _{rss}			-	0.8	-	
Effective Output Capacitance, Energy Related	C _{o(er)}	V _{GS} = 0V, V _{DS} = 0-400V		ı	46	-	pF
Effective Output Capacitance, Time Related	C _{o(tr)}			ı	115	ı	
Output Charge	Q _{oss}			-	46	-	nC
Turn-on Delay Time	t _{d(on)}	$V_{DS} = 400V, I_{D} = 7A,$		-	60	-	
Turn-on Rise Time	t _r			-	18	-	
Turn-Off Delay Time	t _{d(off)}	$V_{GS} = 0.12V, R_G = 47\Omega$		-	80	-	ns
Turn-Off Fall Time	t _f			-	12	-	
Total Gate Charge	Q _g	$V_{DS} = 400V, I_{D} = 7A,$ $V_{GS} = 0-12V$		-	16	-	
Gate-Source Charge	Q_{gs}			ı	4.8	-	nC
Gate-Drain Charge	Q_{gd}			-	4.4	-	
Reverse Diode Characteristics							
	V _{SD}	V _{GS} =0V,	I _S =3.5A	-	1.2	-	
Diode Forward Voltage		V _{GS} =0V,	T _J =25°C	-	1.6	-	V
		I _s =7A	T _J =150°C	-	2	-	
Reverse Recovery Time	t _{rr}	V _{GS} =0V		-	21	-	ns
Reverse Recovery Charge	Q _{rr}	V _{DD} =400V, di/dt=1000A/μs		-	46	-	μC

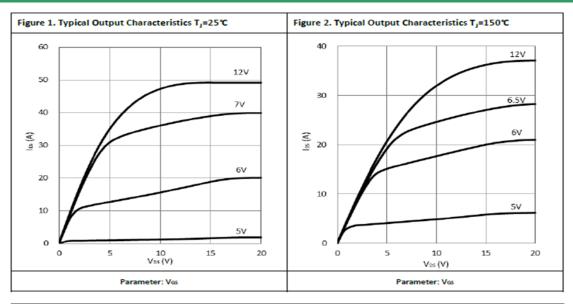
Notes:

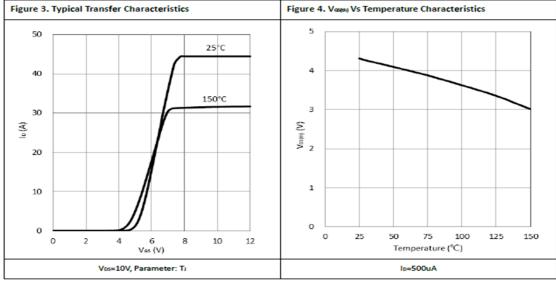
^{1.} Off-state spike duty cycle < 0.01, spike duration < 2μs

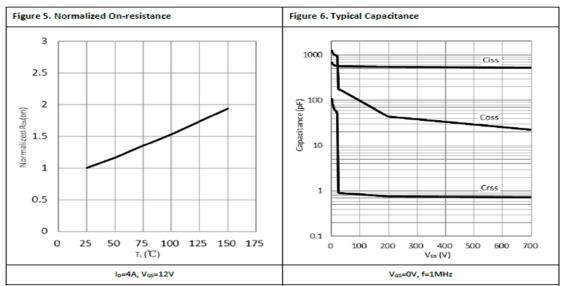
^{2.} Device on one layer epoxy PCB for drain connection (vertical and without air stream cooling, with 6cm²copper area and 70µm thickness)

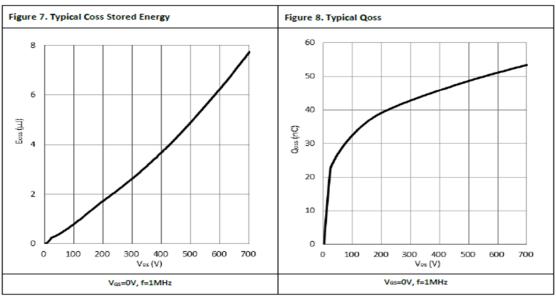
^{3.} Dynamic on-resistance; see Figure 19 and 20 for test circuit and configurations

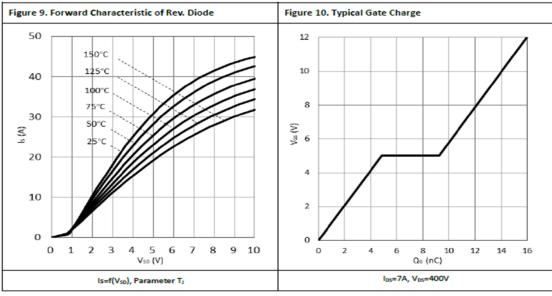
Typical Characteristics

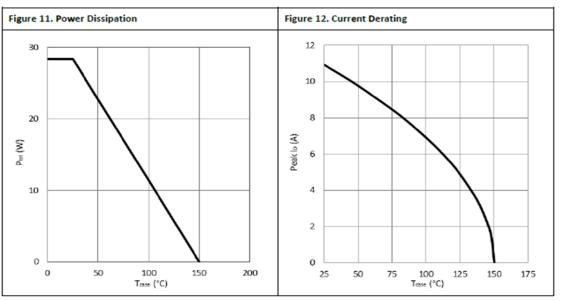


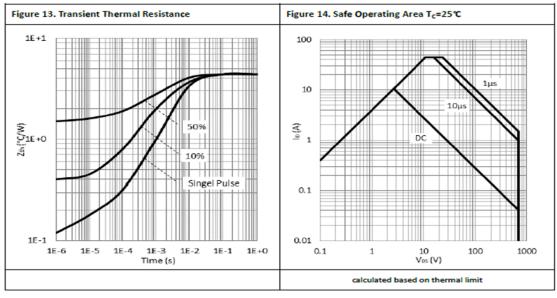


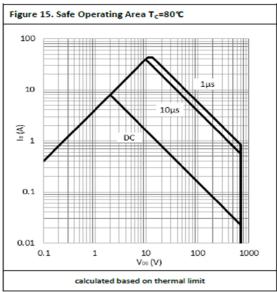




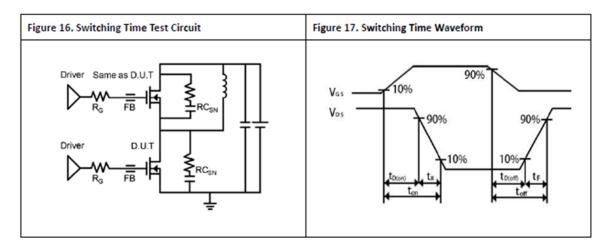


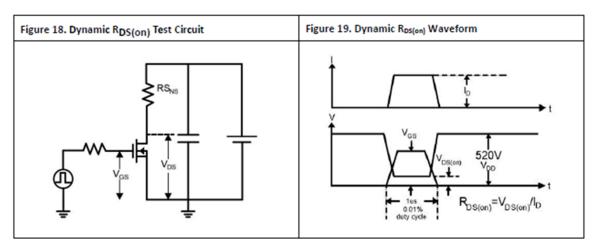


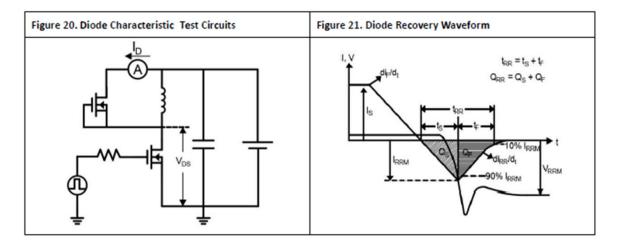




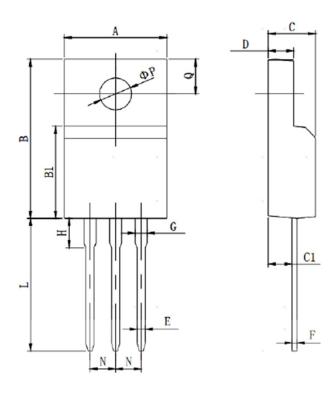
Test Circuits and Waveforms







Product Dimension (TO-220F)



CVMDOL	Millimeter				
SYMBOL	Min	Nom	Max		
Α	9.60	10.00	10.40		
В	15.40	15.80	16.20		
B1	8.90	9.20	9.50		
С	4.30	4.60	4.90		
C1	2.10	2.50	3.00		
D	2.40	2.70	3.00		
E	0.60	0.80	1.00		
F	0.30	0.45	0.60		
G	1.12	1.30	1.42		
Н	3.40	3.60	3.80		
L	12.00	13.00	14.00		
N	2.34	2.54	2.74		
Q	3.15	3.35	3.55		
Р	2.90	3.10	3.30		

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